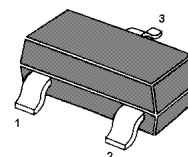
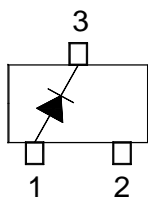


SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply power supply applications

Feature

- Ultra Low V_F




SOT-23 Plastic Package

Marking

Marking Code: FJ

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
DC Reverse Voltage	V_R	20	V
DC Forward Current	I_F	1	A
Peak Forward Surge Current ¹⁾	I_{FSM}	3	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_s	-40 to +125	$^\circ\text{C}$

¹⁾ 60Hz for 1 

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Max	Unit
Forward Voltage at $I_F = 1\text{ A}$	V_F	-	0.45	V
Reverse Current at $V_R = 20\text{ V}$	I_R	-	200	μA

Note: ESD sensitive product handling required.

● **Electrical characteristic curves (Ta=25°C)**

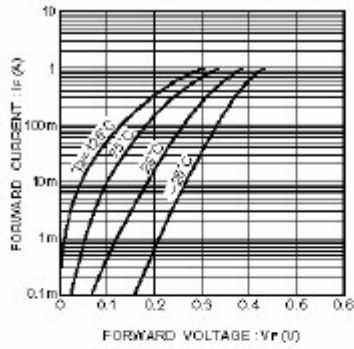


Fig.1 Forward characteristics

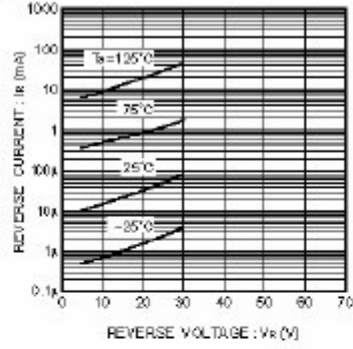


Fig.2 Reverse characteristics

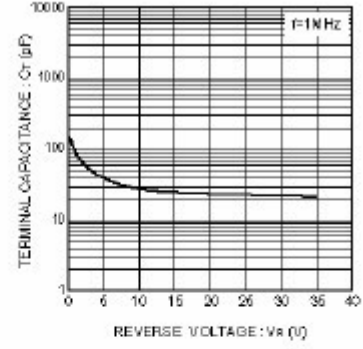


Fig.3 Capacitance between terminals characteristics

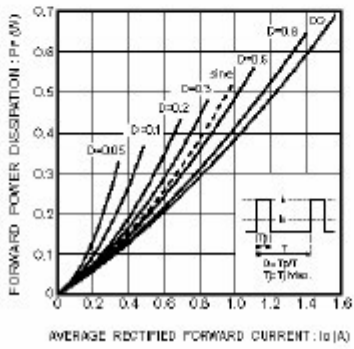


Fig.4 Forward power dissipation characteristics

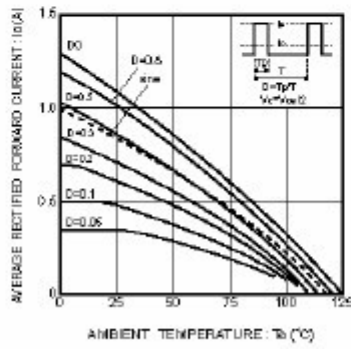


Fig.5 Derating curve ($I_o - T_a$)